# MMBTH10L, MMBTH10-4L, SMMBTH10-4L, NSVMMBTH10L

# **VHF/UHF Transistor**

## **NPN Silicon**

#### **Features**

- S and NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	25	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	30	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	3.0	Vdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ heta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient (Note 2)	$R_{ heta JA}$	417	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

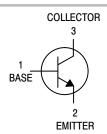
- 1.  $FR-5 = 1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina



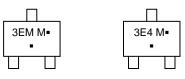
#### ON Semiconductor®

www.onsemi.com





#### **MARKING DIAGRAMS**



MMBTH10LT1G, NSVMMBTH10LT1G MMBTH10-04LT1G

3EM, 3E4= Specific Device Code

M = Date Code\*

Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMBTH10LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
NSVMMBTH10LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTH10-4LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTH10LT3G, SMMBTH10-4LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MMBTH10L, MMBTH10-4L, SMMBTH10-4L, NSVMMBTH10L

### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	<u> </u>				
Collector–Emitter Breakdown Voltage $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	V <sub>(BR)CEO</sub>	25	_	_	Vdc
Collector-Base Breakdown Voltage $(I_C = 100 \mu Adc, I_E = 0)$	V <sub>(BR)CBO</sub>	30	_	_	Vdc
Emitter–Base Breakdown Voltage $(I_E=10~\mu Adc,~I_C=0)$	V <sub>(BR)EBO</sub>	3.0	_	_	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 25 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	-	-	100	nAdc
Emitter Cutoff Current (V <sub>EB</sub> = 2.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	_	100	nAdc
ON CHARACTERISTICS				1	-
DC Current Gain ( $I_C = 4.0 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ ) MMBTH10LT1G, NSVMMBTH10LT1G MMBTH10-4LT1G, SMMBTH10-4LT3G	h <sub>FE</sub>	60 120	_ _	_ 240	-
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 4.0 mAdc, I <sub>B</sub> = 0.4 mAdc)	V <sub>CE(sat)</sub>	-	_	0.5	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = 4.0 mAdc, V <sub>CE</sub> = 10 Vdc)	V <sub>BE</sub>	-	-	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS				•	•
Current–Gain – Bandwidth Product $(I_C = 4.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 100 \text{ Mhz})$ MMBTH10LT1G, NSVMMBTH10LT1G MMBTH10–4LT1G, SMMBTH10–4LT3G	f <sub>T</sub>	650 800	_ _	_ _	MHz
Collector–Base Capacitance $(V_{CB}=10 \text{ Vdc}, I_E=0, f=1.0 \text{ MHz})$	C <sub>cb</sub>	-	_	0.7	pF
Common–Base Feedback Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>rb</sub>	-	-	0.65	pF
Collector Base Time Constant (I <sub>C</sub> = 4.0 mAdc, V <sub>CB</sub> = 10 Vdc, f = 31.8 MHz)	rb′C <sub>c</sub>	-	_	9.0	ps

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## MMBTH10L, MMBTH10-4L, SMMBTH10-4L, NSVMMBTH10L

### **TYPICAL CHARACTERISTICS**

### **COMMON-BASE y PARAMETERS versus FREQUENCY**

 $(V_{CB} = 10 \text{ Vdc}, I_{C} = 4.0 \text{ mAdc}, T_{A} = 25^{\circ}\text{C})$ 

### $y_{ib}$ , INPUT ADMITTANCE

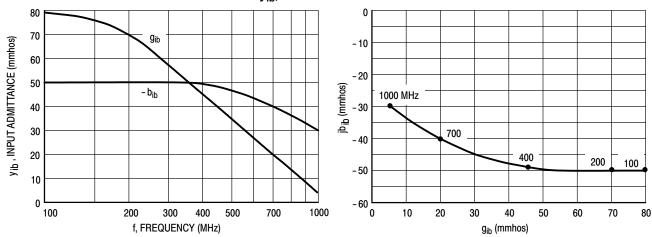


Figure 1. Rectangular Form

Figure 2. Polar Form

### y<sub>fb</sub>, FORWARD TRANSFER ADMITTANCE

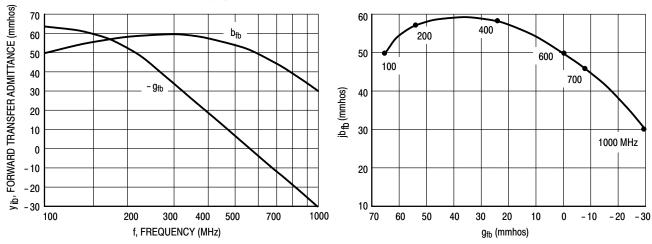


Figure 3. Rectangular Form

Figure 4. Polar Form

# MMBTH10L, MMBTH10-4L, SMMBTH10-4L, NSVMMBTH10L

#### **TYPICAL CHARACTERISTICS**

### **COMMON-BASE y PARAMETERS versus FREQUENCY**

 $(V_{CB} = 10 \text{ Vdc}, I_C = 4.0 \text{ mAdc}, T_A = 25^{\circ}\text{C})$ 

### y<sub>rb</sub>, REVERSE TRANSFER ADMITTANCE

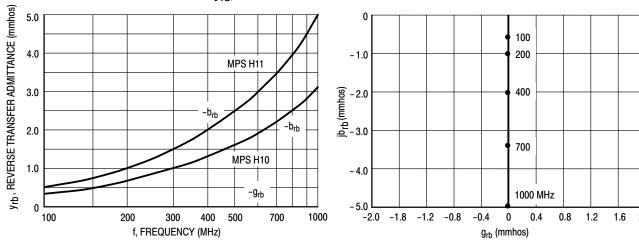


Figure 5. Rectangular Form

Figure 6. Polar Form

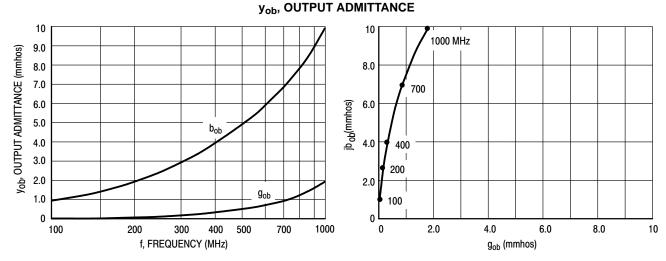


Figure 7. Rectangular Form

Figure 8. Polar Form

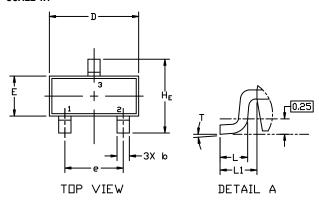


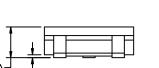


SOT-23 (TO-236) **CASE 318 ISSUE AT** 

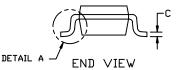
**DATE 01 MAR 2023** 







SIDE VIEW



#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

## **GENERIC MARKING DIAGRAM\***

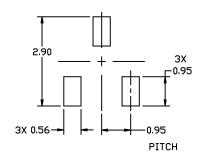


XXX = Specific Device Code

= Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

### **STYLES ON PAGE 2**

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Reposit Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-23 (TO-236)		PAGE 1 OF 2	

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.



### **SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ı	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE		PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE		2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE		3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	I PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-23 (TO-236)		PAGE 2 OF 2

onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI., and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent\_Marking.pdf">www.onsemi.com/site/pdf/Patent\_Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer p

#### ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales



# 单击下面可查看定价,库存,交付和生命周期等信息

>>ON Semiconductor(安森美)